



SLP8N65S / SLF8N65S

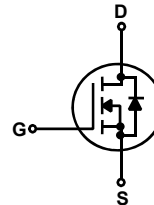
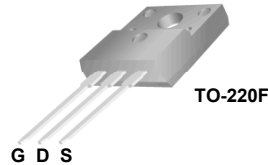
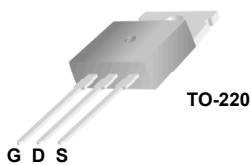
SLP8N65S / SLF8N65S 650V N-Channel MOSFET

General Description

This Power MOSFET is produced using Maple semi's advanced planar stripe DMOS technology. This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency switched mode power supplies, active power factor correction based on half bridge topology.

Features

- 7.5A, 650V, $R_{DS(on)} = 1.4\Omega @ V_{GS} = 10V$
- Low gate charge (typical 48nC)
- High ruggedness
- Fast switching
- 100% avalanche tested
- Improved dv/dt capability



Absolute Maximum Ratings T_C = 25°C unless otherwise noted

Symbol	Parameter	SLP8N65S	SLF8N65S	Units
V _{DSS}	Drain-Source Voltage	650		V
I _D	Drain Current	- Continuous (T _C = 25°C)	7.5	A
		- Continuous (T _C = 100°C)	4.6	A
I _{DM}	Drain Current - Pulsed (Note 1)	21		A
V _{GSS}	Gate-Source Voltage	±30		V
E _{AS}	Single Pulsed Avalanche Energy (Note 2)	128		mJ
I _{AR}	Avalanche Current (Note 1)	7.5		A
E _{AR}	Repetitive Avalanche Energy (Note 1)	12.6		mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)	3.3		V/ns
P _D	Power Dissipation (T _C = 25°C) - Derate above 25°C	78	35	W
		0.62	0.28	W/°C
T _J , T _{STG}	Operating and Storage Temperature Range	-55 to +150		°C
T _L	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds	300		°C

Thermal Characteristics

Symbol	Parameter	Max		Units
		SLP8N65S	SLF8N65S	
R _{θJC}	Thermal Resistance, Junction-to-Case	1.6	3.57	°C/W
R _{θJA}	Thermal Resistance, Junction-to-Ambient	62.5	62.5	°C/W

Electrical Characteristics $T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
Off Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	650	--	--	V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = 250\text{ }\mu\text{A}$, Referenced to 25°C	--	0.64	--	$\text{V}/^\circ\text{C}$
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 650\text{ V}, V_{GS} = 0\text{ V}$	--	--	10	μA
		$V_{DS} = 520\text{ V}, T_C = 125^\circ\text{C}$	--	--	100	μA
I_{GSSF}	Gate-Body Leakage Current, Forward	$V_{GS} = 30\text{ V}, V_{DS} = 0\text{ V}$	--	--	100	nA
I_{GSSR}	Gate-Body Leakage Current, Reverse	$V_{GS} = -30\text{ V}, V_{DS} = 0\text{ V}$	--	--	-100	nA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	2.0	--	4.0	V
$R_{DS(on)}$	Static Drain-Source On-Resistance	$V_{GS} = 10\text{ V}, I_D = 3.75\text{ A}$	--	1.2	1.4	Ω
g_{FS}	Forward Transconductance	$V_{DS} = 40\text{ V}, I_D = 3.75\text{ A}$ (Note 4)	--	7.5	--	S
Dynamic Characteristics						
C_{iss}	Input Capacitance	$V_{DS} = 25\text{ V}, V_{GS} = 0\text{ V}, f = 1.0\text{ MHz}$	--	1100	--	pF
C_{oss}	Output Capacitance		--	251	--	pF
C_{riss}	Reverse Transfer Capacitance		--	14	--	pF
Switching Characteristics						
$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 300\text{ V}, I_D = 7.5\text{ A}, R_G = 25\text{ }\Omega$ (Note 4, 5)	--	15.2	--	ns
t_r	Turn-On Rise Time		--	20	--	ns
$t_{d(off)}$	Turn-Off Delay Time		--	46	--	ns
t_f	Turn-Off Fall Time		--	22	--	ns
Q_g	Total Gate Charge	$V_{DS} = 520\text{ V}, I_D = 7.5\text{ A}, V_{GS} = 10\text{ V}$ (Note 4, 5)	--	48	--	nC
Q_{gs}	Gate-Source Charge		--	7	--	nC
Q_{gd}	Gate-Drain Charge		--	7.4	--	nC
Drain-Source Diode Characteristics and Maximum Ratings						
I_S	Maximum Continuous Drain-Source Diode Forward Current		--	--	7.5	A
I_{SM}	Maximum Pulsed Drain-Source Diode Forward Current		--	--	21	A
V_{SD}	Drain-Source Diode Forward Voltage	$V_{GS} = 0\text{ V}, I_S = 7.5\text{ A}$	--	--	1.4	V
t_{rr}	Reverse Recovery Time	$V_{GS} = 0\text{ V}, I_S = 7.5\text{ A}$	--	320	--	ns
Q_{rr}	Reverse Recovery Charge	$di_F / dt = 100\text{ A}/\mu\text{s}$ (Note 4)	--	3.7	--	μC

Notes:

1. Repetitive Rating : Pulse width limited by maximum junction temperature
2. $L=1\text{mH}, I_{AS} = 16\text{A}, V_{DD} = 50\text{V}, R_G = 25\Omega$, Starting $T_J = 25^\circ\text{C}$
3. $I_{SD} \leq 7.5\text{A}, di/dt \leq 300\text{A}/\mu\text{s}, V_{DD} \leq BV_{DSS}$, Starting $T_J = 25^\circ\text{C}$
4. Pulse Test : Pulse width $\leq 300\mu\text{s}$, Duty cycle $\leq 2\%$
5. Essentially independent of operating temperature

Typical Characteristics

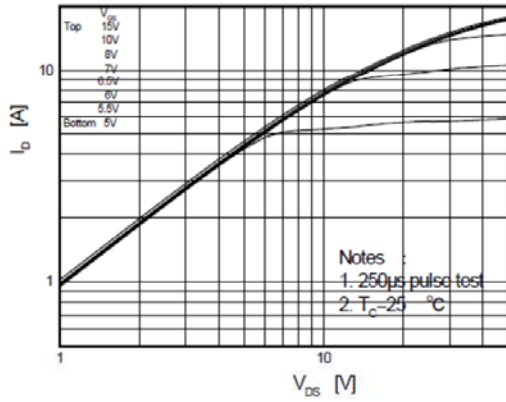


Figure 1. On-Region Characteristics

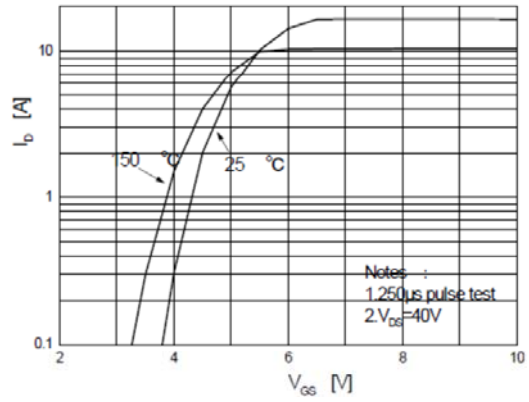


Figure 2. Transfer Characteristics

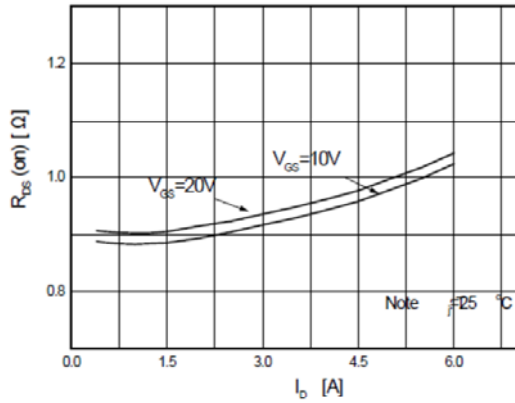


Figure 3. On-Resistance Variation vs Drain Current and Gate Voltage

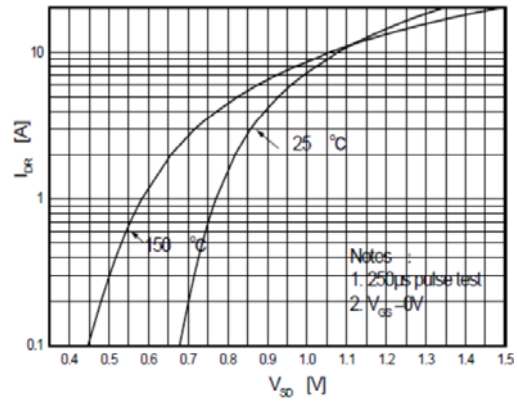


Figure 4. Body Diode Forward Voltage Variation with Source Current and Temperature

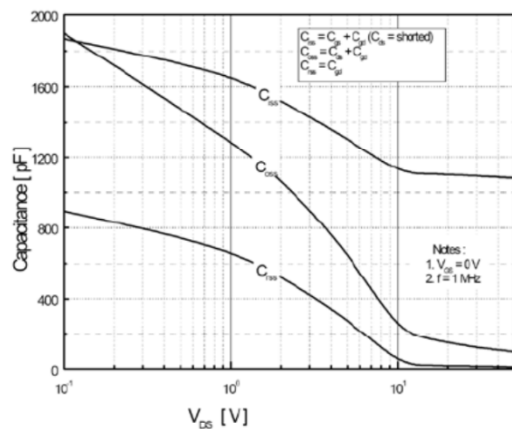


Figure 5. Capacitance Characteristics

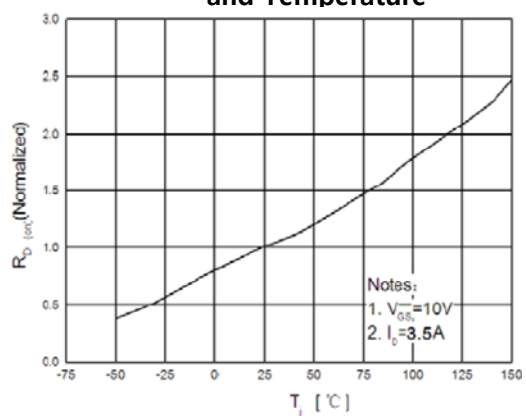


Figure 6. On-Resistance Variation vs Temperature

Typical Characteristics (Continued)

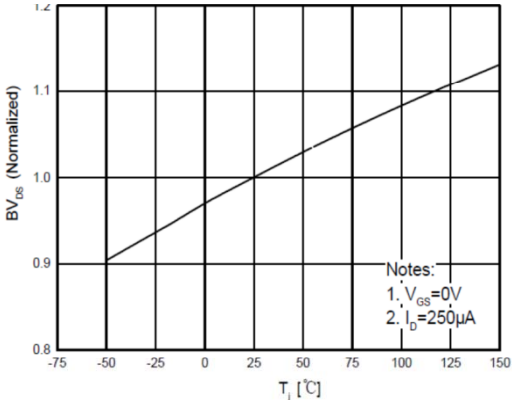
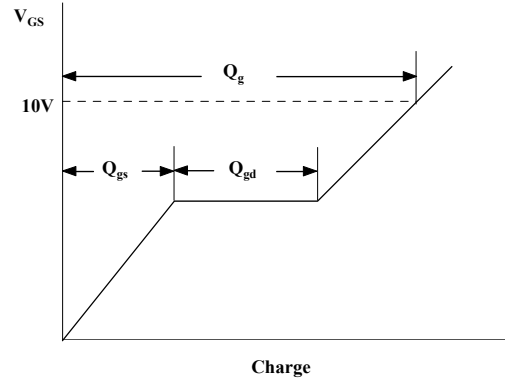
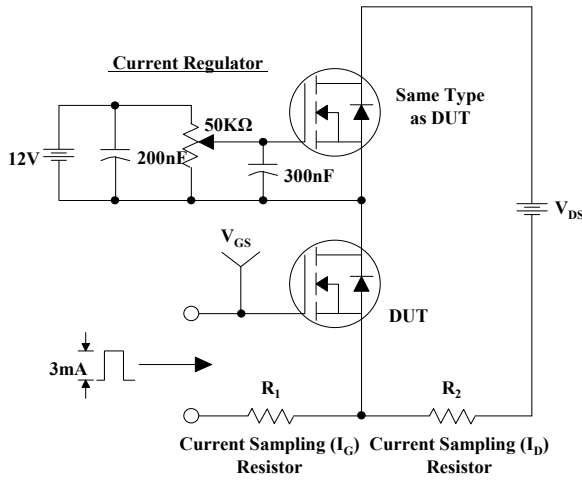
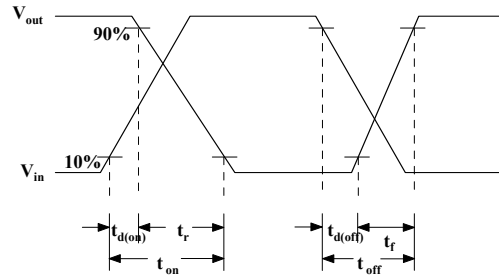
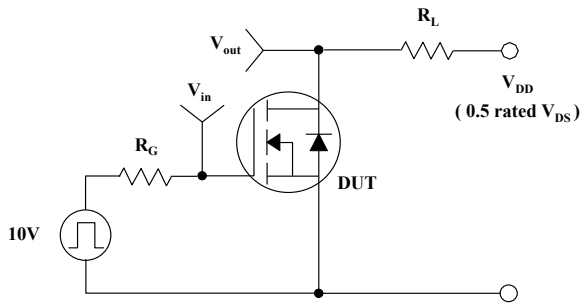


Figure 7. Breakdown Voltage Variation vs Temperature

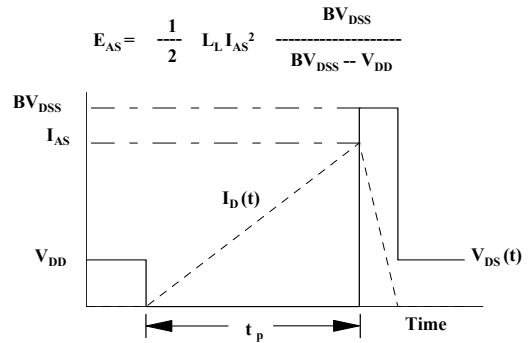
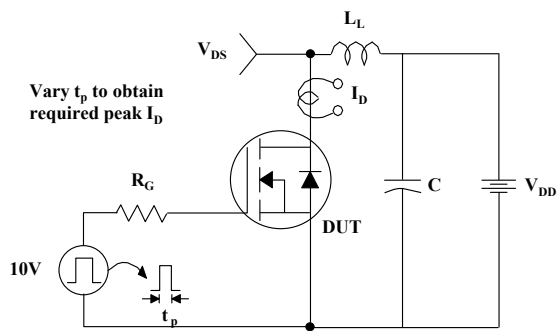
Gate Charge Test Circuit & Waveform



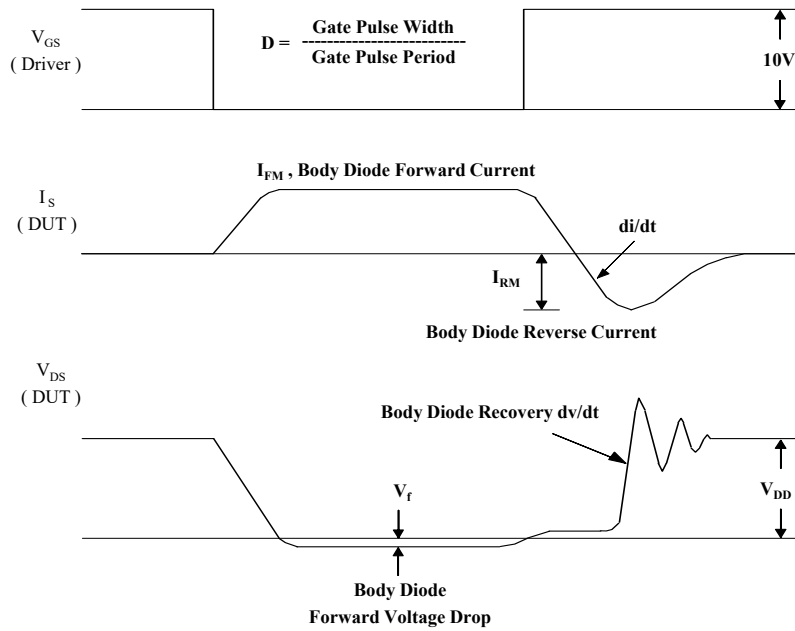
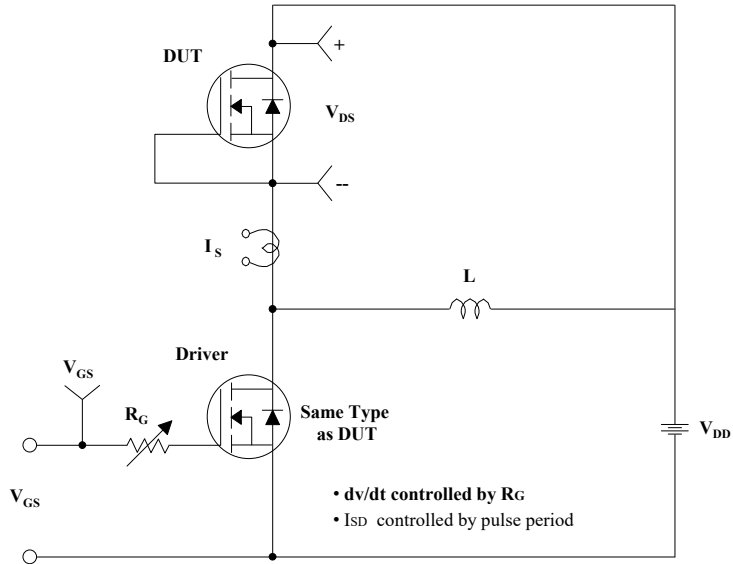
Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching Test Circuit & Waveforms



Peak Diode Recovery dv/dt Test Circuit & Waveforms



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